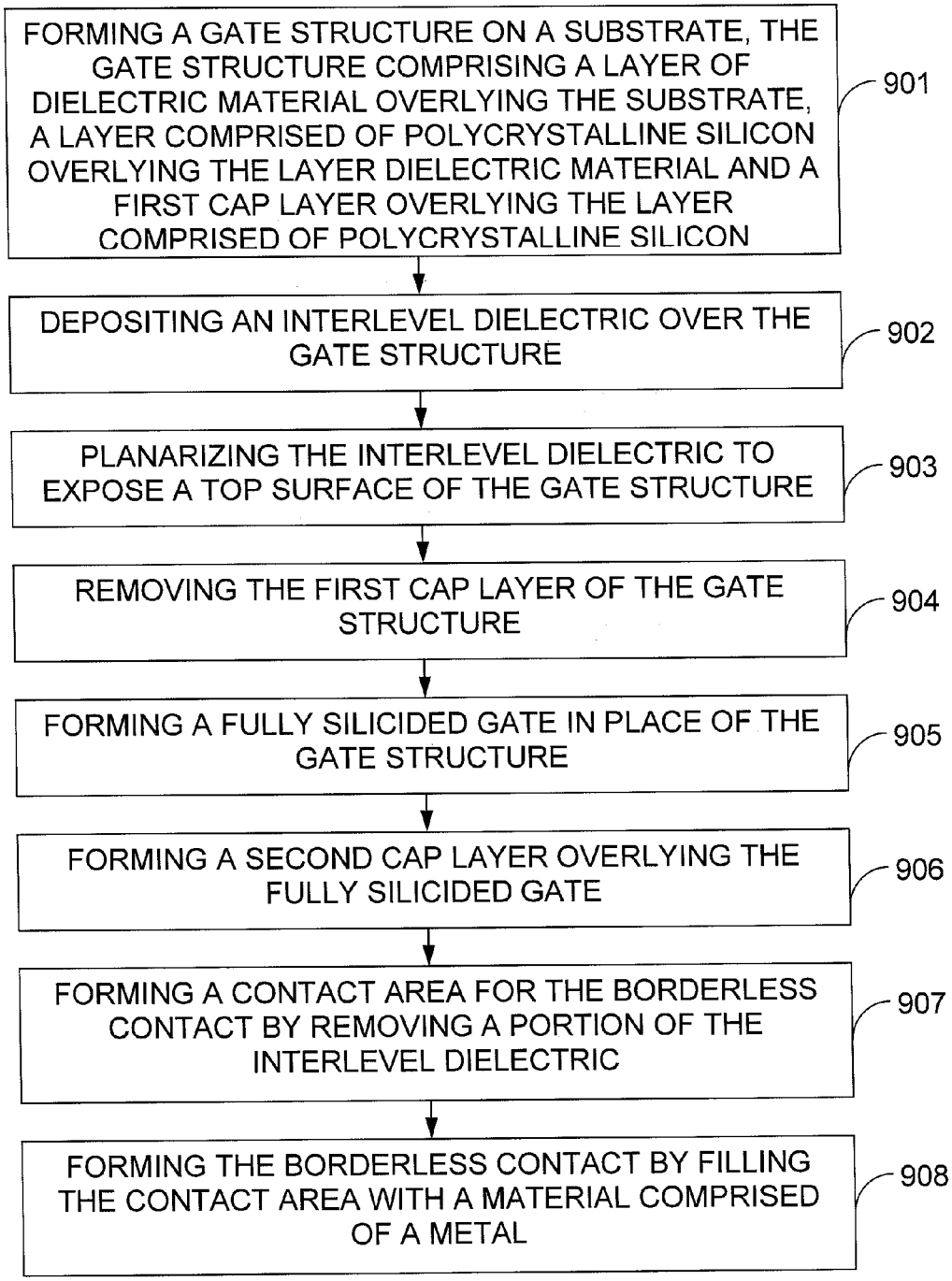
FORMING A GATE STRUCTURE ON A SUBSTRATE, THE GATE STRUCTURE COMPRISING A LAYER OF DIELECTRIC MATERIAL OVERLYING THE SUBSTRATE, A LAYER COMPRISED OF POLYCRYSTALLINE SILICON OVERLYING THE LAYER DIELECTRIC MATERIAL AND A FIRST CAP LAYER OVERLYING THE LAYER COMPRISED OF POLYCRYSTALLINE SILICON
901
DEPOSITING AN INTERLEVEL DIELECTRIC OVER THE GATE STRUCTURE
902
PLANARIZING THE INTERLEVEL DIELECTRIC TO EXPOSE A TOP SURFACE OF THE GATE STRUCTURE
903
REMOVING THE FIRST CAP LAYER OF THE GATE STRUCTURE
904
FORMING A FULLY SILICIDED GATE IN PLACE OF THE GATE STRUCTURE
905
FORMING A SECOND CAP LAYER OVERLYING THE FULLY SILICIDED GATE
906
FORMING A CONTACT AREA FOR THE BORDERLESS CONTACT BY REMOVING A PORTION OF THE INTERLEVEL DIELECTRIC
907
FORMING THE BORDERLESS CONTACT BY FILLING THE CONTACT AREA WITH A MATERIAL COMPRISED OF A METAL
908

FIG. 36